

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a ferroelectric capacitor, comprising:
  - forming a lower electrode on a ~~base~~substrate;
  - forming a ferroelectric film which includes a lead zirconate titanate niobate (PZTN) complex oxide including lead, zirconium, titanium, and niobium on the lower electrode;
  - forming an upper electrode on the ferroelectric film;
  - forming a ~~protective-silicon oxide~~ film without providing a hydrogen barrier film so as to cover the lower electrode, the ferroelectric film, and the upper electrode; and
  - performing heat treatment for crystallizing the PZTN complex oxide at least after forming the ~~protective-silicon oxide~~ film.
2. (Currently Amended) The method of manufacturing a ferroelectric capacitor as defined in claim 1,
  - ~~wherein~~ the PZTN complex oxide ~~is~~being in an amorphous state after pre-heat treatment in an oxidizing atmosphere and before the heat treatment in the step of forming the ferroelectric film.
3. (Currently Amended) The method of manufacturing a ferroelectric capacitor as defined in claim 1,
  - ~~wherein the protective film is a silicon oxide film and~~ the silicon oxide film is being formed by using trimethylsilane.

4. (Currently Amended) The method of manufacturing a ferroelectric capacitor as defined in claim 1,

~~wherein~~ the heat treatment for crystallizing the PZTN complex oxide ~~is~~ being performed in a non-oxidizing atmosphere.

5.-7. (Canceled)